



#### SIHP17N80E-GE3 Information



For Reference Only

Part Number SIHP17N80E-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CHAN 850V TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **SIHP17N80E-GE3 Specifications**

Manufacturer Part Number         SIHP17N80E-GE3           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         E           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         800V           Current - Continuous Drain (Id) @ 25°C         15A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         122nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2408pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         208W (Tc)           Rds On (Max) @ Id, Vgs         290 mOhm @ 8.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C15A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs122nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2408pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs290 mOhm @ 8.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  15A (Tc)  15V  15V  15V  15V  15V  15V  15V  15	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs122nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2408pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)208W (Tc)Rds On (Max) @ Id, Vgs290 mOhm @ 8.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id       4V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       122nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       2408pF @ 100V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       208W (Tc)         Rds On (Max) @ Id, Vgs       290 mOhm @ 8.5A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       TO-220AB         Package / Case       TO-220-3	Current - Continuous Drain (Id) @ 25°C	15A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  2408pF @ 100V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  290 mOhm @ 8.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
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FET Feature - Common Co	Input Capacitance (Ciss) (Max) @ Vds	2408pF @ 100V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  290 mOhm @ 8.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs290 mOhm @ 8.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Power Dissipation (Max)	208W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	290 mOhm @ 8.5A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### SIHP17N80E-GE3 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **SIHP17N80E-GE3 Payment Methods**



















# SIHP17N80E-GE3 Shipping Methods













If you have any question about SIHP17N80E-GE3, please do not hesitate to contact us!

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